



P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low R_{DS(ON)}:
 - $80 \text{ m}\Omega$ @V_{GS} = -4.5V
 - 110 m Ω @V_{GS} = -2.7V
 - 130 m Ω @V_{GS} = -2.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

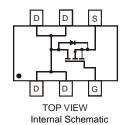
Mechanical Data

- Case: SOT-26
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate)

SOT-26







Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 1) Continuous	$T_A = 25$ °C $T_A = 70$ °C	I _D	-3.4 -2.7	А
Pulsed Drain Current (Note 2)		I _{DM}	-12	A
Body-Diode Continuous Current (Note 1)		Is	2.0	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	1.25	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{ hetaJA}$	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤10s.
- 2. Repetitive Rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

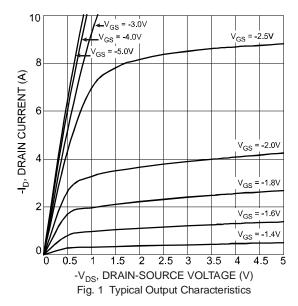


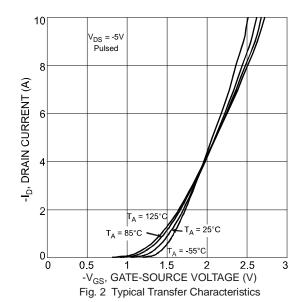
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_		V	$I_D = -250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Body Leakage Current	I_{GSS}	_		±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$
Gate Threshold Voltage	V _{GS(th)}	-0.6		-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
On State Drain Current (Note 5)	I _{D (ON)}	-15			Α	$V_{GS} = -4.5V, V_{DS} = -5V$
			51	80		$V_{GS} = -4.5V$, $I_D = -4.5A$
Static Drain-Source On-Resistance (Note 5)	R _{DS} (ON)	_	82 94	110 130	mΩ	$V_{GS} = -2.7V$, $I_D = -3.8A$
	, í					$V_{GS} = -2.5V$, $I_D = -3.7A$
Forward Transconductance (Note 5)	g FS	_	6.3	_	S	$V_{DS} = -10V, I_{D} = -4.5A$
Diode Forward Voltage (Note 5)		_	0.79	-1.26	V	$I_S = -1.7A$, $V_{GS} = 0V$
Maximum Body-Diode Continuous Current (Note 1)		_		1.7	Α	_
DYNAMIC PARAMETERS (Note 6)						
Total Gate Charge	Q_g	_	7.3	_	nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$
Gate-Source Charge	Q_{gs}	_	2.0		nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$
Gate-Drain Charge	Q_{gd}	_	1.9		nC	$V_{GS} = -4.5V$, $V_{DS} = -10V$, $I_D = 4.5A$
Turn-On Delay Time	t _{D(on)}	_	12		ns	
Turn-On Rise Time	t _r	_	20		ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(off)}	_	38	_	ns	$R_L = 10\Omega$, $R_G = 6\Omega$
Turn-Off Fall Time	t _f	_	41		ns	
Input Capacitance	C _{iss}	_	443	_	pF	10// // 0//
Output Capacitance	Coss	_	125		pF	$V_{DS} = -16V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		98	_	pF	1 - 1.0IVII IZ

Notes:

- 5. Test pulse width $t=300\mu s$. 6. Guaranteed by design. Not subject to production testing.







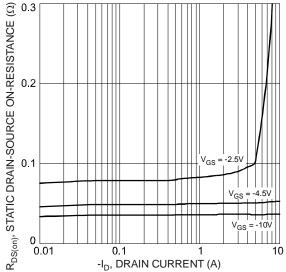


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

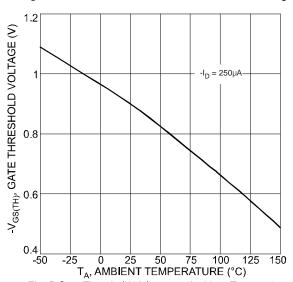


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

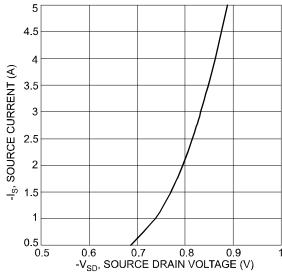
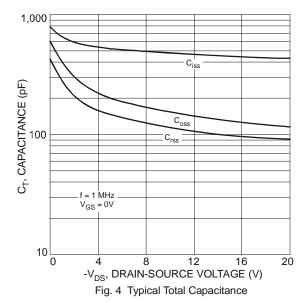


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



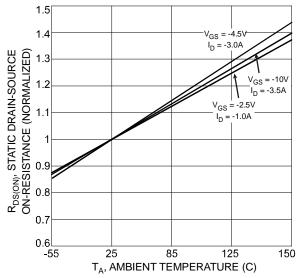


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

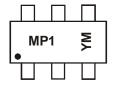


Ordering Information (Note 7)

Part Number	Case	Packaging
DMP2130LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

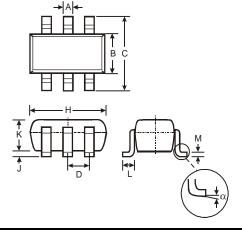


MP1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

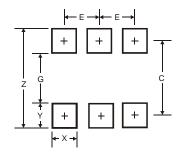
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Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
၁	2.70	3.00	2.80			
D			0.95			
H	2.90	3.10	3.00			
۲	0.013	0.10	0.05			
K	1.00	1.30	1.10			
Г	0.35	0.55	0.40			
М	0.10	0.20	0.15			
α	0°	8°				
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
С	2.40
Е	0.95

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